



DVR5V0W

COMPLEX ARRAY FOR VOLTAGE REGULATORS

Features

- Epitaxial Planar Die Construction
- Selectively Paired NPN Transistors & Zener Diodes for Series Pass Voltage Regulator Circuits
- Ideally Suited for Automated Assembly Processes
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)

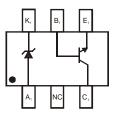
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

SOT363



Top View



Top View Pin Configuration

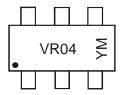
Ordering Information (Note 3)

Device	Packaging	Shipping
DVR5V0W-7	SOT363	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



VR04 = Product Type Marking Code YM = Date Code Marking Y = Year ex: Y = 2011 M = Month ex: 9 = September

Date Code Key

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	R	S	T	U	٧	W	Х	Υ	Z	Α	В	С

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings, Total Device @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	P_d	200	mW
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Maximum Ratings, NPN Transistor @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	45	V
Collector-Emitter Voltage	V _{CEO}	18	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current - Continuous (Note 4	l _C	1	A

Maximum Ratings, Zener Element @T_A = 25°C unless otherwise specified

	Characteristic	Symbol	Value	Unit
Forward Voltage	@ I _F = 10mA	V _F	0.9	V

Electrical Characteristics, NPN Transistor @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	•				
Collector-Base Breakdown Voltage	V _{(BR)CBO}	45	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	18	_	V	$I_C = 1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	1	μА	V _{CB} = 40V, I _E = 0
Emitter Cutoff Current	I _{EBO}	_	1	μΑ	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h _{FE}	150	800	_	$I_C = 100 \text{mA}, V_{CE} = 1 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.5	V	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}		8	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$
Current Gain-Bandwidth Product	f _T	100	_	MHz	$V_{CB} = 10V, I_E = 50mA, f = 100MHz$

Electrical Characteristics, Zener Element @T_A = 25°C unless otherwise specified

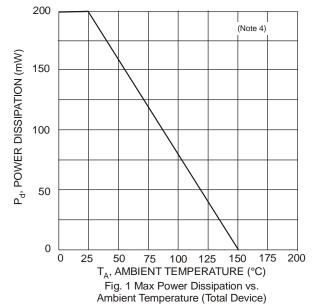
	Zener Voltage Range (Note 6)				Reverse Current 5)
	V _Z @ I _{ZT}			I _R @ \	V _R
Nom (V)	Min (V)	Max (V)	mA	μΑ	V
5.1	4.85	5.36	0.05	5	3

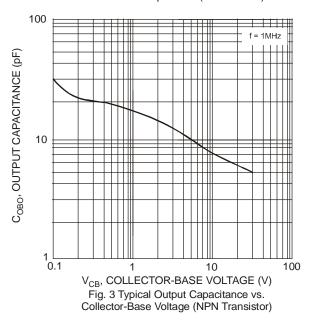
Notes: 4. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

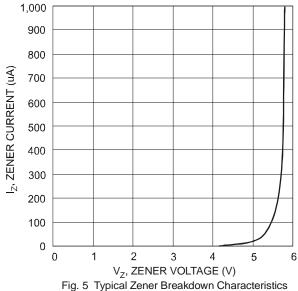
5. Short duration pulse test used to minimize self-heating effect.

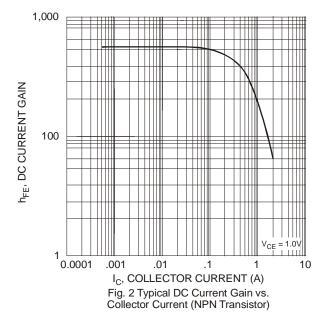
6. Nominal Zener voltage is measured with the device junction in thermal equilibrium at $T_T = 30^{\circ}\text{C} \pm 1^{\circ}\text{C}$.











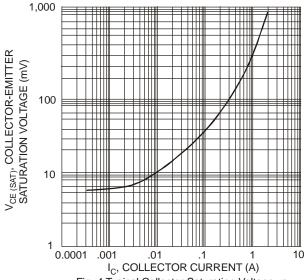
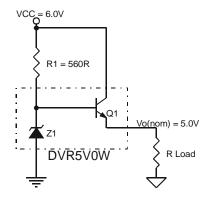


Fig. 4 Typical Collector Saturation Voltage vs. Collector Current (NPN Transistor)



Sample Applications



Sample Application for DVR5V0W:

 $V_{CC} = 6.0V$ R1= 560Ω

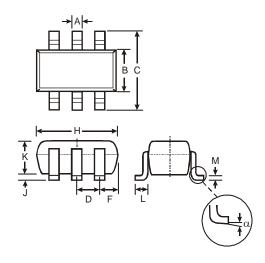
 $Vo(nom) = 5.0V \qquad I_O = 100mA$

Notes: 7. Resistor R1 not included.

8. Typical performance shown is under setup and operating conditions specified in the sample applications.

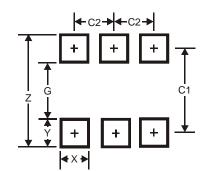
9. Recommended V_{CC}(min) ~ Vo(nom) + 1V.

Package Outline Dimensions



	SOT363						
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
С	2.00	2.20					
D	0.65 Typ						
F	0.40	0.45					
Н	1.80	2.20					
J	0	0.10					
K	0.90	1.00					
L	0.25	0.40					
М	0.10	0.22					
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65



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 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
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